

Medium stress SiNx Films, Grown using Unaxis ICP Tool, as well as PECVD Tool, Characterizations

	100 °C (ICP)	250 °C (ICP)	250 °C (PECVD)
Refractive Index	~2	~2	~2
Deposition Rate (nm/min)	21.9	21.2	~13
Buffered HF Etch Rate (nm/min)	120	72	36
Stress (~200-nm Film on a Si Wafer) (MPa)	-344	-387	260